

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A silicon carbide product comprising a single-crystalline or polycrystalline silicon carbide, wherein the single-crystalline or polycrystalline silicon carbide is cleaned only by an acidic solution, the single-crystalline or polycrystalline silicon carbide having a surface with a concentration of metal impurities equal to or less than 1×10^{11} ~~[[()]]~~atoms/cm² ~~[[()]]~~.

2. (Original) The silicon carbide product according to claim 1, wherein said metal impurities are at least one of iron or an iron compound, Ni, and Cu.

3. (Currently Amended) The silicon carbide product according to claim 1 or 2, ~~wherein characterized in that~~ wherein said product is at least one of a semiconductor device, a semiconductor device manufacturing member, and a structure.

4. (Currently Amended) A silicon carbide product cleaning method comprising ~~the step of immersing a single-crystalline or polycrystalline silicon carbide in an acid, wherein the step of immersing the single-crystalline or polycrystalline silicon carbide in the acidic solution to reduce~~ reduces surface metal impurities of the single-crystalline or polycrystalline silicon carbide to 1×10^{11} ~~[[()]]~~ atoms/cm² ~~[[()]]~~ or less.

5. (Currently Amended) A method of manufacturing a silicon carbide product composed of a single-crystalline or polycrystalline silicon carbide, comprising:
forming a single-crystalline or polycrystalline silicon carbide; and
~~the step of cleaning silicon carbide with~~ the single-crystalline or polycrystalline silicon carbide only by an acidic solution ~~an acid~~ to reduce surface metal impurities to 1×10^{11} ~~[[()]]~~atoms/cm² ~~[[()]]~~ or less.

6. (Original) The method according to claim 5, wherein said acid is hydrofluoric acid or hydrochloric acid.

7. (Original) The method according to claim 6, wherein said hydrofluoric acid has a concentration exceeding 45%.

8. (Original) The method according to claim 7, wherein said hydrofluoric acid has a concentration of about 50%.

9. (Original) The method according to claim 6, wherein said hydrochloric acid has a concentration of 35% or more.

10. (Original) The method according to claim 9, wherein said hydrochloric acid has a concentration of about 36%.

11. (Original) The method according to claim 5, wherein said acid is a liquid containing sulfuric acid and a hydrogen peroxide solution.

12. (Original) The method according to claim 11, wherein said liquid containing said sulfuric acid and said hydrogen peroxide solution has a pH of 4 or less.

13. (Original) The method according to claim 12, wherein said sulfuric acid and said hydrogen peroxide solution respectively have concentrations of about 97% and about 30% and are mixed in a volume ratio of about 4:1.

14. (Original) A silicon carbide product manufactured by the method according to claim 5, said silicon carbide product being a semiconductor device, a semiconductor device manufacturing member, or a structure.

15. (New) The method according to claim 5, wherein the step of forming single-crystalline or polycrystalline silicon carbide comprises:

growing a polycrystalline silicon carbide layer over a whole of a graphite base member by a CVD method; and

separating the polycrystalline silicon carbide layer from the graphite base member by burning out the graphite base member to form the silicon carbide product.

16 (New) The method according to claim 5, wherein the step of forming single-crystalline or polycrystalline silicon carbide comprises:

providing a base member; and

growing the single-crystalline or polycrystalline silicon carbide over the base member.